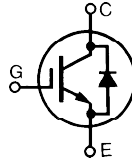


# High Voltage, BiMOSFET™ Monolithic Bipolar MOS Transistor

## IXBT42N300HV IXBH42N300HV

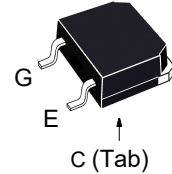


$$V_{CES} = 3000V$$

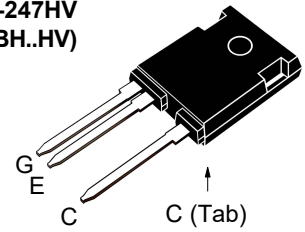
$$I_{C110} = 42A$$

$$V_{CE(sat)} \leq 3.0V$$

TO-268HV  
(IXBT..HV)



TO-247HV  
(IXBH..HV)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

| Symbol                                  | Test Conditions  | Maximum Ratings       |            |
|---|--|-----------------------|------------|
| $V_{CES}$                               | $T_C = 25^\circ C$ to $150^\circ C$  | 3000                  | V          |
| $V_{CGR}$                               | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$                                      | 3000                  | V          |
| $V_{GES}$                               | Continuous   | $\pm 25$              | V          |
| $V_{GEM}$                               | Transient  | $\pm 35$              | V          |
| $I_{C25}$                               | $T_C = 25^\circ C$   | 104                   | A          |
| $I_{C110}$                              | $T_C = 110^\circ C$  | 42                    | A          |
| $I_{CM}$                                | $T_C = 25^\circ C$ , 1ms   | 400                   | A          |
| <b>SSOA</b><br><b>(RBSOA)</b>           | $V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 20\Omega$<br>Clamped Inductive Load           | $I_{CM} = 84$<br>1500 | A<br>V     |
| <b>T<sub>sc</sub></b><br><b>(SCSOA)</b> | $V_{GE} = 15V$ , $T_J = 125^\circ C$ ,<br>$R_G = 82\Omega$ , $V_{CE} = 1500V$ , Non-Repetitive | 10                    | $\mu s$    |
| $P_C$                                   | $T_C = 25^\circ C$   | 500                   | W          |
| $T_J$                                   |  | -55 ... +150          | $^\circ C$ |
| $T_{JM}$                                |  | 150                   | $^\circ C$ |
| $T_{stg}$                               |  | -55 ... +150          | $^\circ C$ |
| $T_L$                                   | Maximum Lead Temperature for Soldering   | 300                   | $^\circ C$ |
| $T_{SOLD}$                              | Plastic Body for 10s   | 260                   | $^\circ C$ |
| $M_d$                                   | Mounting Torque (TO-247HV)   | 1.13/10               | Nm/lb.in   |
| <b>Weight</b>                           | TO-268HV   | 4                     | g          |
|   | TO-247HV   | 6                     | g          |

### Features

- High Voltage Package
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage
- FBSOA
- SCSOA

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications

- Laser Generators
- Capacitor Discharge Circuits
- AC Switches
- Protection Circuits

| Symbol        | Test Conditions<br>( $T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values |            |                       |
|---------------|---|-----------------------|------------|-----------------------|
|               |   | Min.                  | Typ.       | Max.                  |
| $BV_{CES}$    | $I_C = 1mA$ , $V_{GE} = 0V$   | 3000                  |            | V                     |
| $V_{GE(th)}$  | $I_C = 1mA$ , $V_{CE} = V_{GE}$                                     | 3.0                   |            | 5.0 V                 |
| $I_{CES}$     | $V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$<br>$T_J = 125^\circ C$ |                       | 250        | 50 $\mu A$<br>$\mu A$ |
| $I_{GES}$     | $V_{CE} = 0V$ , $V_{GE} = \pm 25V$                                  |                       |            | $\pm 200$ nA          |
| $V_{CE(sat)}$ | $I_C = 42A$ , $V_{GE} = 15V$ , Note 1<br>$T_J = 125^\circ C$        |                       | 2.5<br>3.1 | 3.0 V<br>V            |

| Symbol Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified) |  | Characteristic Values |      |                         |
|--|--|-----------------------|------|-------------------------|
|  |  | Min.                  | Typ. | Max.                    |
| $g_{fs}$   | $I_C = 42\text{A}, V_{CE} = 10\text{V}$ , Note 1   | 28                    | 45   | S                       |
| $C_{ies}$  | } $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$   |                       | 4780 | pF                      |
| $C_{oes}$  |  |                       | 170  | pF                      |
| $C_{res}$  |  |                       | 56   | pF                      |
| $R_{Gi}$   | Gate Input Resistance  |                       | 3.0  | $\Omega$                |
| $Q_g$  | } $I_C = 42\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$   |                       | 200  | nC                      |
| $Q_{ge}$   |  |                       | 28   | nC                      |
| $Q_{gc}$   |  |                       | 75   | nC                      |
| $t_{d(on)}$  | } <b>Resistive Switching Times, <math>T_J = 25^\circ\text{C}</math></b><br>$I_C = 42\text{A}, V_{GE} = 15\text{V}$<br>$V_{CE} = 1500\text{V}, R_G = 20\Omega$  |                       | 72   | ns                      |
| $t_r$  |  |                       | 330  | ns                      |
| $t_{d(off)}$   |  |                       | 445  | ns                      |
| $t_f$  |  |                       | 610  | ns                      |
| $t_{d(on)}$  | } <b>Resistive Switching Times, <math>T_J = 125^\circ\text{C}</math></b><br>$I_C = 42\text{A}, V_{GE} = 15\text{V}$<br>$V_{CE} = 1500\text{V}, R_G = 20\Omega$ |                       | 72   | ns                      |
| $t_r$  |  |                       | 580  | ns                      |
| $t_{d(off)}$   |  |                       | 460  | ns                      |
| $t_f$  |  |                       | 490  | ns                      |
| $R_{thJC}$   |  |                       |      | 0.25 $^\circ\text{C/W}$ |
| $R_{thCS}$   | TO-247HV   |                       | 0.21 | $^\circ\text{C/W}$      |

### Reverse Diode

| Symbol Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified) |   | Characteristic Values |      |               |
|--|---|-----------------------|------|---------------|
|  |   | Min.                  | Typ. | Max.          |
| $V_F$  | $I_F = 42\text{A}, V_{GE} = 0\text{V}$ , Note 1   |                       |      | 2.5 V         |
| $t_{rr}$   | } $I_F = 21\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}, V_{GE} = 0\text{V}$ |                       | 1.7  | $\mu\text{s}$ |
| $I_{RM}$   |   |                       | 43   | A             |

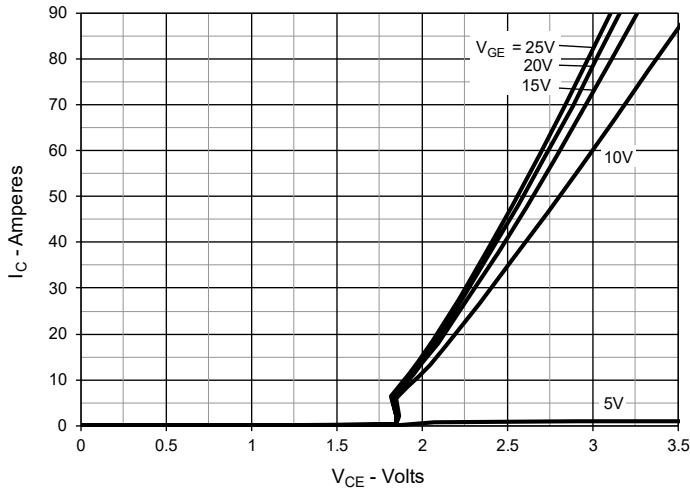
Note 1. Pulse test,  $t < 300\mu\text{s}$ , duty cycle,  $d < 2\%$ .

Littelfuse reserves the right to change limits, test conditions and dimensions.

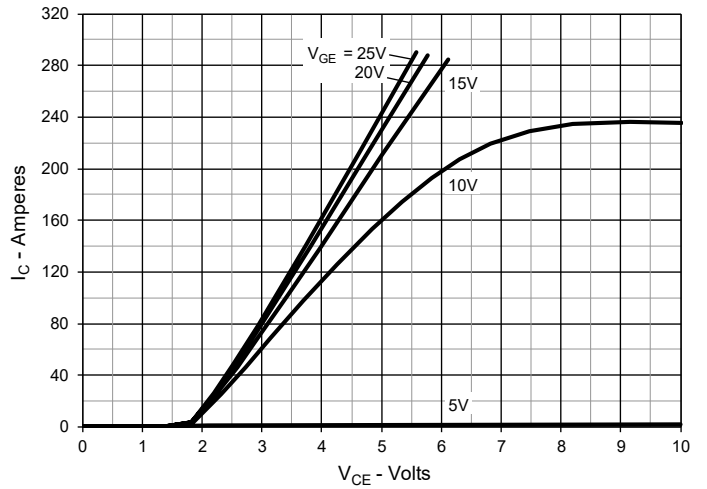
LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

|           |           |           |           |              |              |              |              |              |              |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|--------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338 B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |              |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |              |

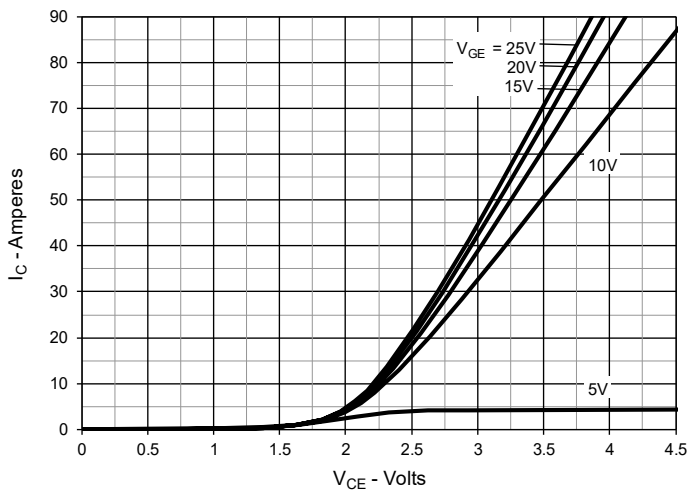
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



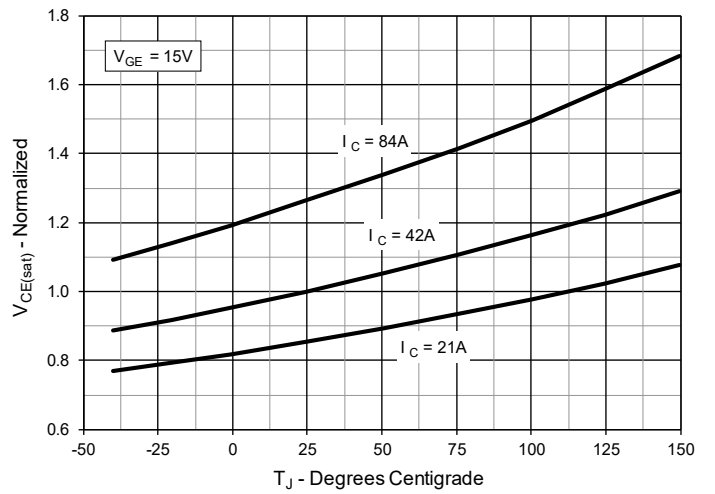
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



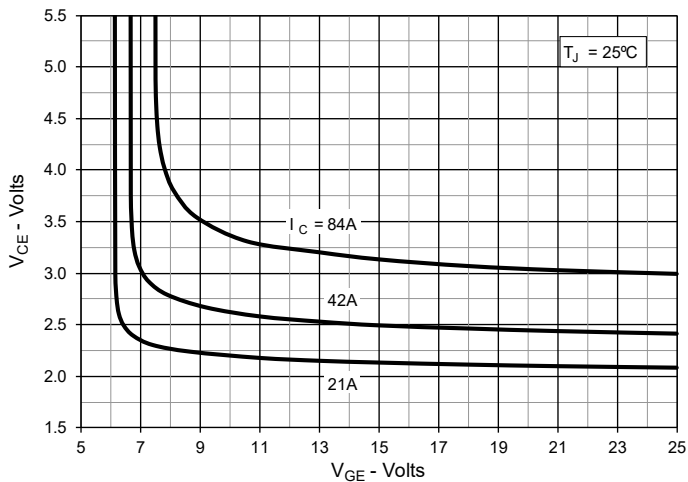
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



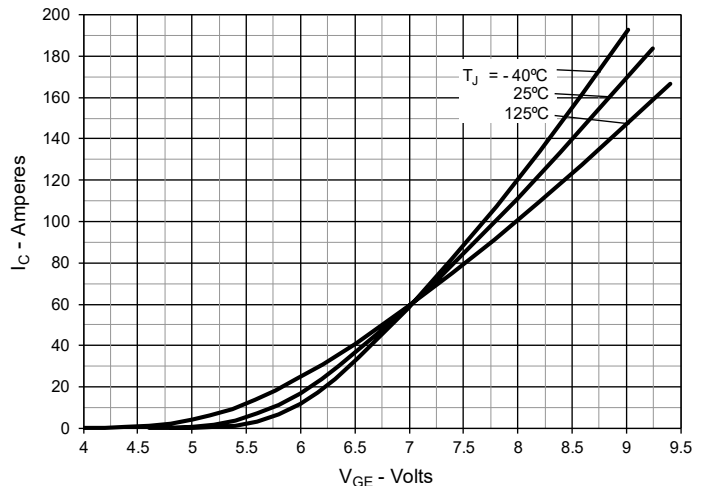
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



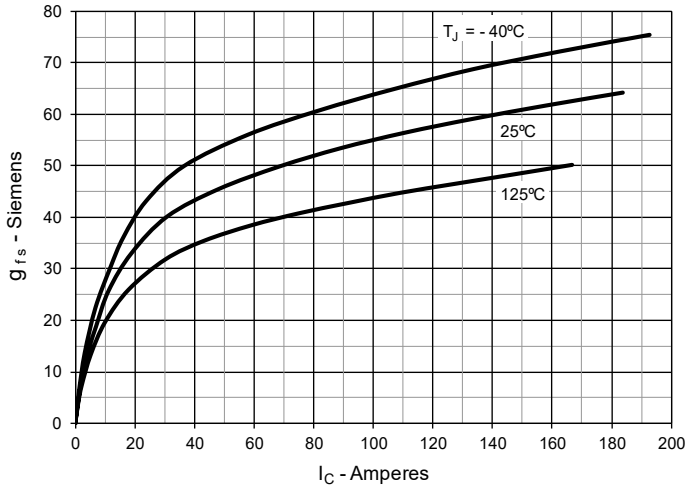
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



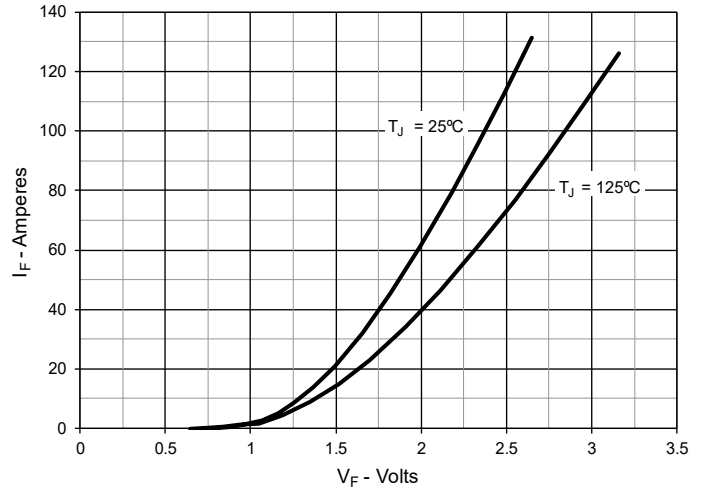
**Fig. 6. Input Admittance**



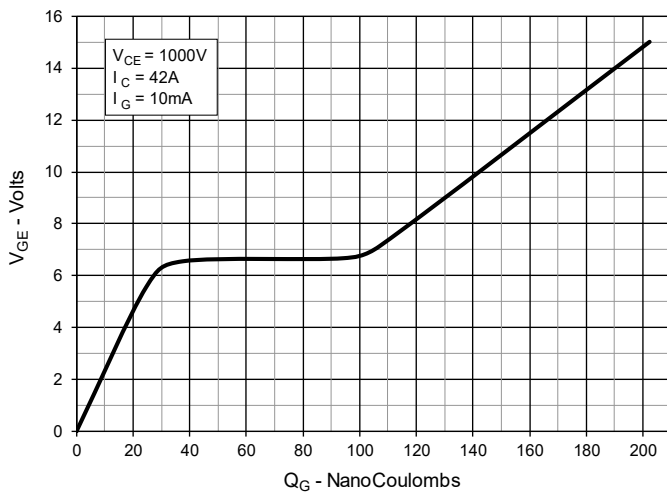
**Fig. 7. Transconductance**



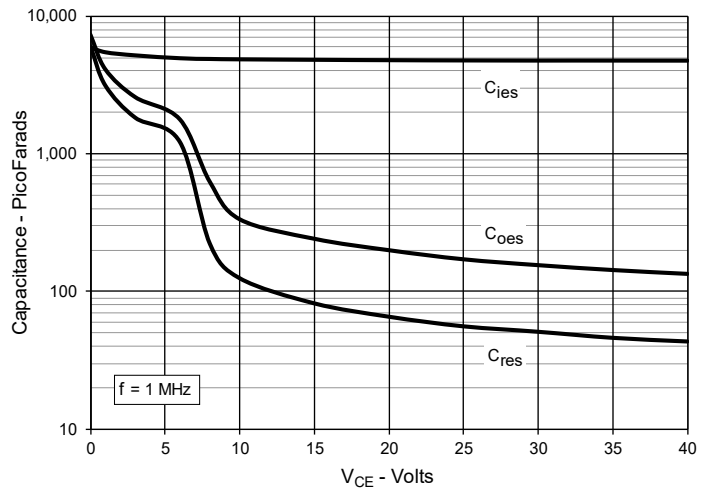
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



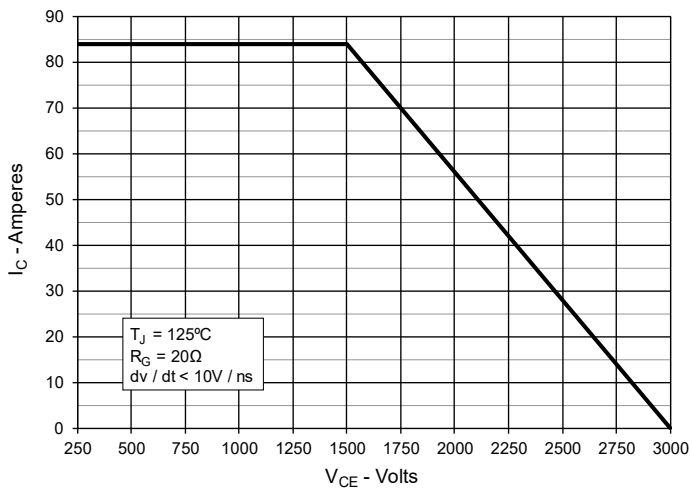
**Fig. 9. Gate Charge**



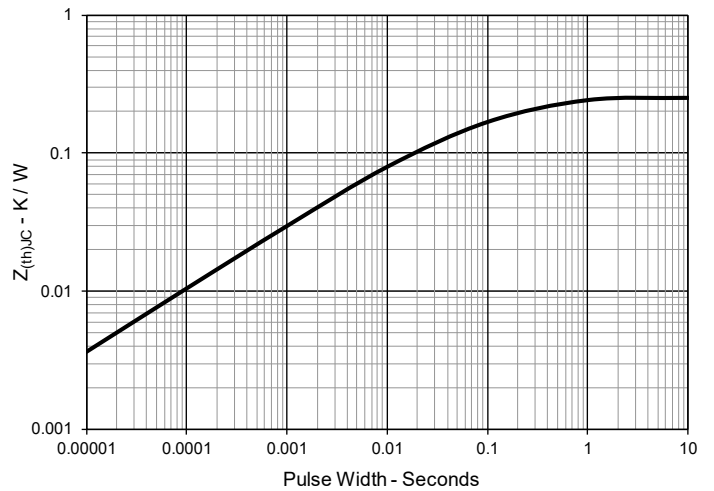
**Fig. 10. Capacitance**



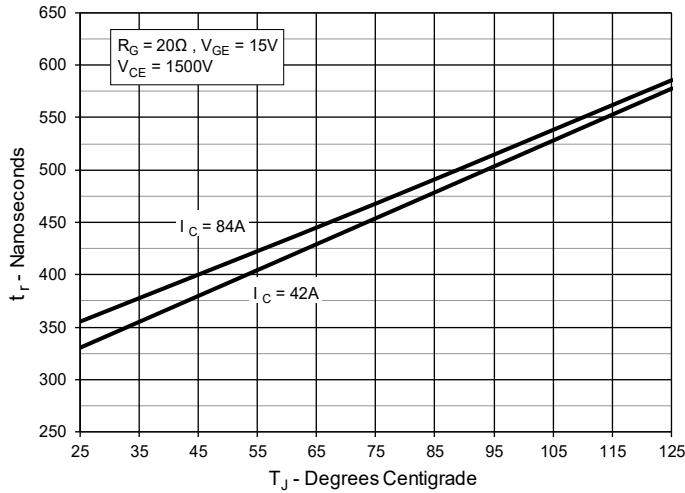
**Fig. 11. Reverse-Bias Safe Operating Area**



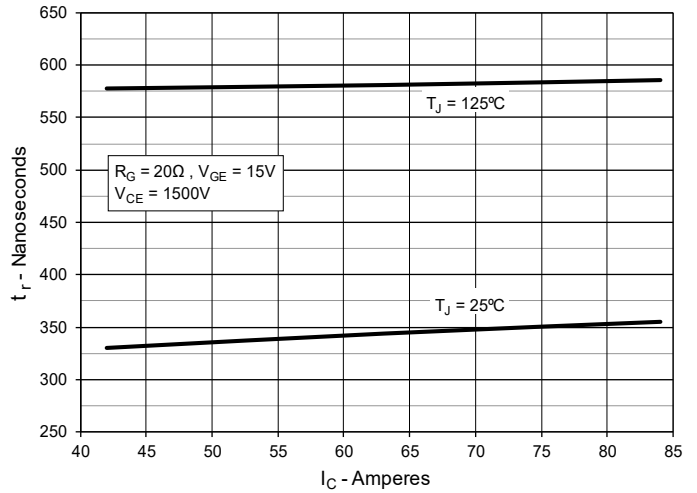
**Fig. 12. Maximum Transient Thermal Impedance**



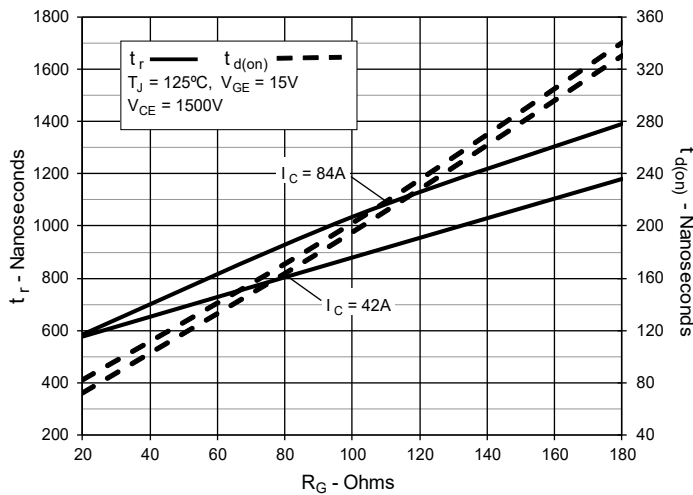
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



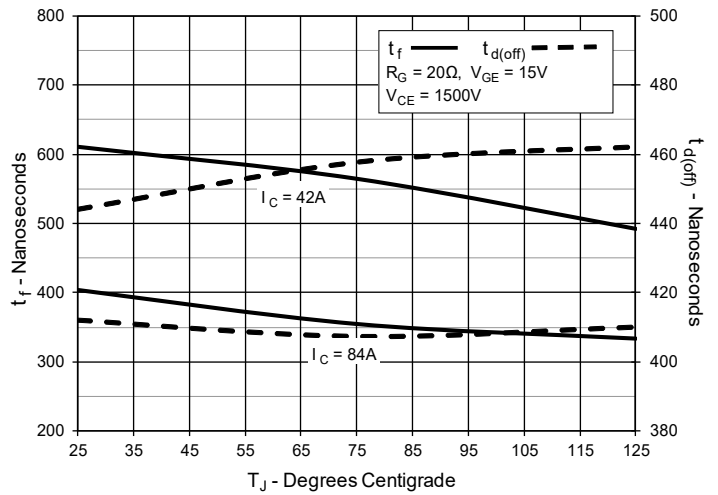
**Fig. 14. Resistive Turn-on Rise Time vs. Collector Current**



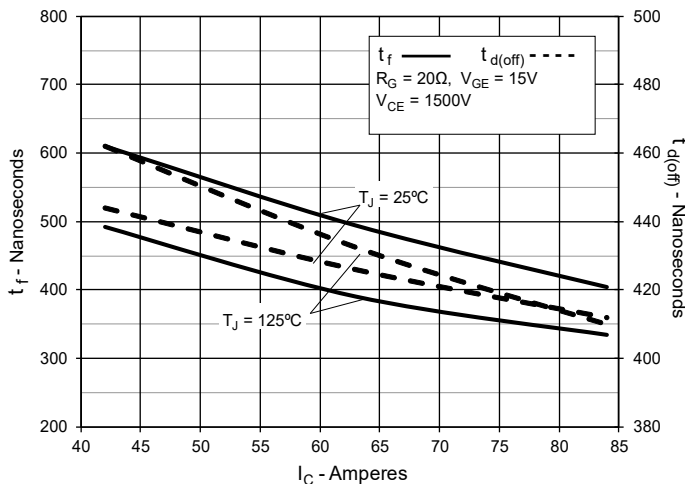
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



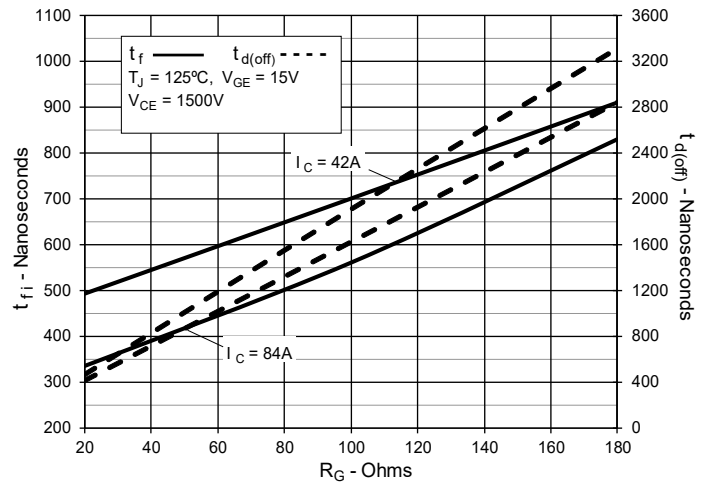
**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



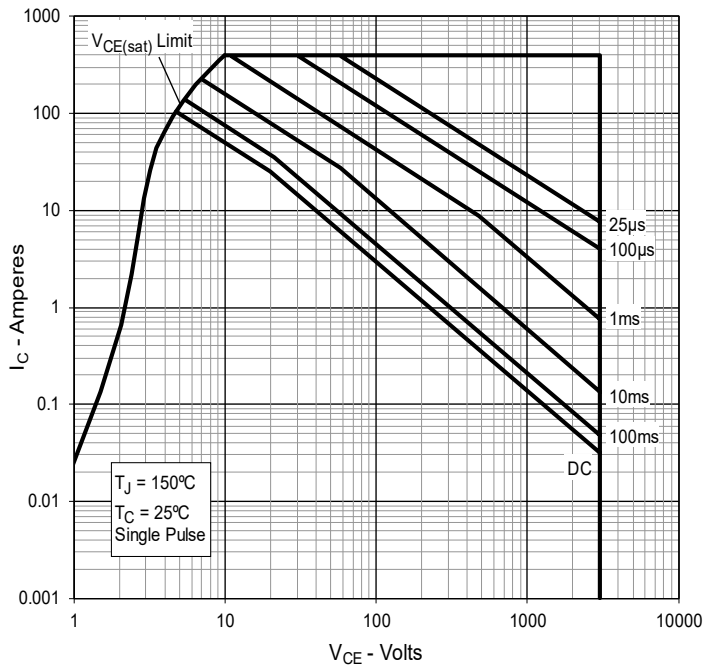
**Fig. 17. Resistive Turn-off Switching Times vs. Collector Current**



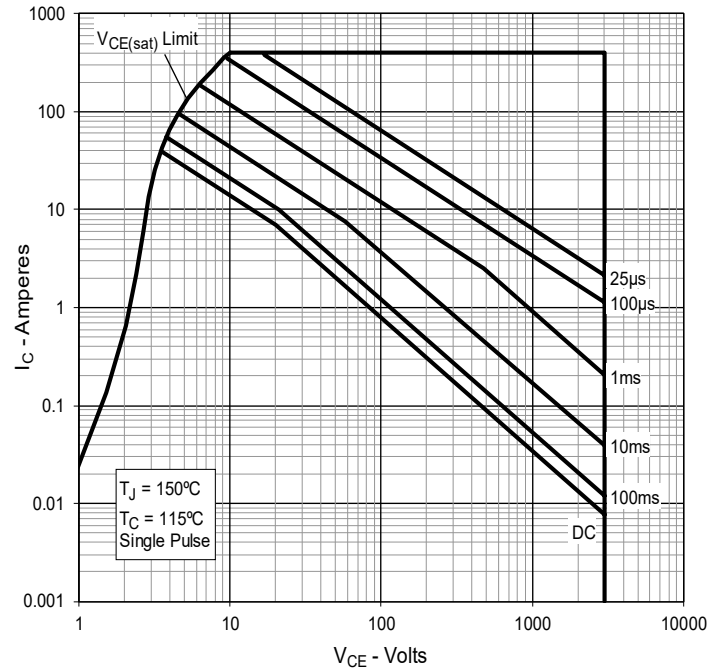
**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**



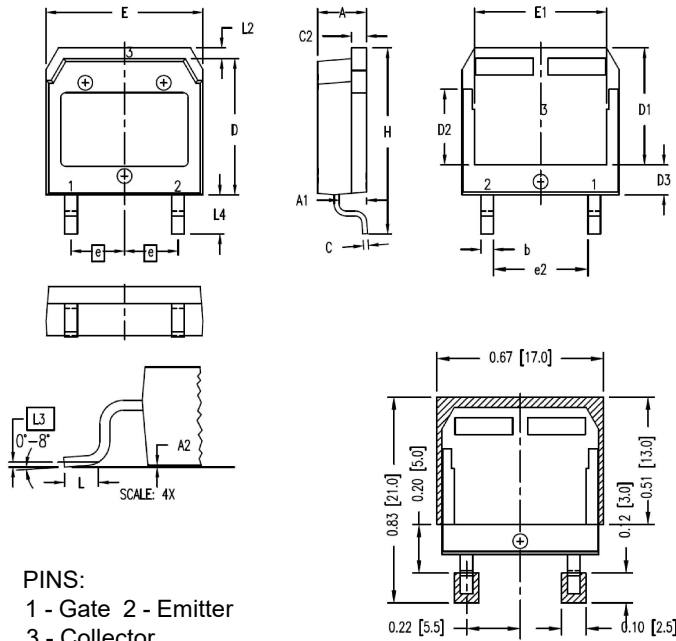
**Fig. 19. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$**



**Fig. 20. Forward-Bias Safe Operating Area @  $T_C = 115^\circ\text{C}$**



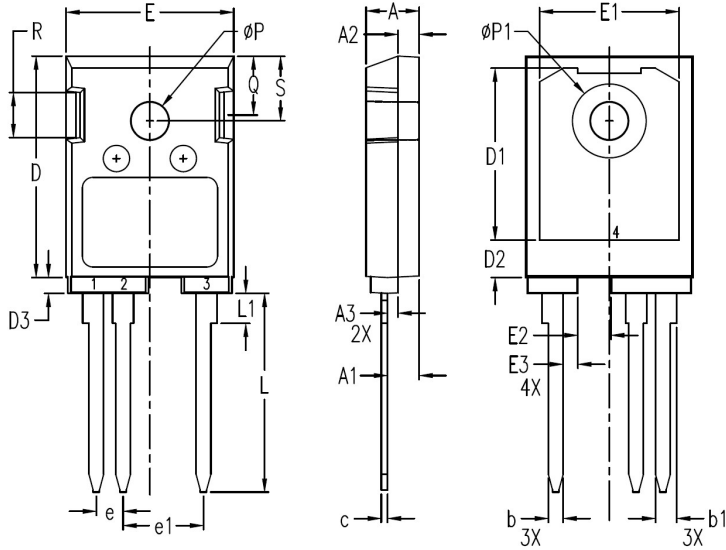
### TO-268HV Outline



PINS:  
1 - Gate 2 - Emitter  
3 - Collector

| SYM  | INCHES   |      | MILLIMETER |       |
|------|----------|------|------------|-------|
|      | MIN      | MAX  | MIN        | MAX   |
| A    | .193     | .201 | 4.90       | 5.10  |
| A1   | .106     | .114 | 2.70       | 2.90  |
| A2   | .001     | .010 | 0.02       | 0.25  |
| b    | .045     | .057 | 1.15       | 1.45  |
| C    | .016     | .026 | 0.40       | 0.65  |
| C2   | .057     | .063 | 1.45       | 1.60  |
| D    | .543     | .551 | 13.80      | 14.00 |
| D1   | .465     | .476 | 11.80      | 12.10 |
| D2   | .295     | .307 | 7.50       | 7.80  |
| D3   | .114     | .126 | 2.90       | 3.20  |
| E    | .624     | .632 | 15.85      | 16.05 |
| E1   | .524     | .535 | 13.30      | 13.60 |
| e    | .215 BSC |      | 5.45 BSC   |       |
| (e2) | .374     | .386 | 9.50       | 9.80  |
| H    | .736     | .752 | 18.70      | 19.10 |
| L    | .067     | .079 | 1.70       | 2.00  |
| L2   | .039     | .045 | 1.00       | 1.15  |
| L3   | .010 BSC |      | 0.25 BSC   |       |
| L4   | .150     | .161 | 3.80       | 4.10  |

### TO-247HV Outline



PINS:  
1 - Gate 2 - Emitter  
3,4 - Collector

| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .193     | .201 | 4.90        | 5.10  |
| A1  | .114     | .122 | 2.90        | 3.10  |
| A2  | .075     | .083 | 1.90        | 2.10  |
| A3  | .035     | .043 | 0.90        | 1.10  |
| b   | .053     | .059 | 1.35        | 1.50  |
| b1  | .075     | .083 | 1.90        | 2.10  |
| c   | .022     | .030 | 0.55        | 0.75  |
| D   | .819     | .843 | 20.80       | 21.40 |
| D1  | .638     | .646 | 16.20       | 16.40 |
| D2  | .134     | .146 | 3.40        | 3.70  |
| D3  | .055     | .063 | 1.40        | 1.60  |
| E   | .622     | .638 | 15.80       | 16.20 |
| E1  | .520     | .528 | 13.20       | 13.40 |
| E2  | .118     | .126 | 3.00        | 3.20  |
| E3  | .051     | .059 | 1.30        | 1.50  |
| e   | .100 BSC |      | 2.54 BSC    |       |
| e1  | .300 BSC |      | 7.62 BSC    |       |
| L   | .724     | .748 | 18.40       | 19.00 |
| L1  | .106     | .118 | 2.70        | 3.00  |
| øP  | .138     | .142 | 3.50        | 3.60  |
| øP1 | .272     | .280 | 6.90        | 7.10  |
| Q   | .216     | .224 | 5.50        | 5.70  |
| R   | .165     | .169 | 4.20        | 4.30  |
| S   | .240     | .248 | 6.10        | 6.30  |



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